

the spacer is provided. FIG. 20 shows an experimental example 1 (the case where the spacer is absent), FIG. 21 shows an experimental example 2 (the case where the spacer is provided at the entire periphery), FIG. 22 shows an experimental example 3 (the case where the spacer is provided at the right semicircular portion), and FIG. 23 shows an experimental example 4 (the case where the spacer is provided at the left semicircular portion).

[0042]

(Experimental Example 1)

FIG. 20 is a list showing the evaluation result of an experimental example 1 (the case where the spacer is absent). Part (a) of FIG. 20 shows a map showing an etching rate. Part (b) of FIG. 20 shows a graph showing a normalized etching rate. Part (c) of FIG. 20 shows the position into which the spacer is inserted. Part (d) of FIG. 20 shows the effect. The four angles ( $0^\circ$ ,  $45^\circ$ ,  $90^\circ$ ,  $315^\circ$ ) shown in Part (b) of FIG. 20 are directions in which an etching rate of the substrate (target object) shown in FIG. 20 Part (a) is measured.

In the case of the experimental example 1, as apparent from Part (b) of FIG. 20, the normalized etching rates are significantly different from each other in four angles. That is, in the experimental example 1, it is seen that, the etching rate with respect to the target object is highly dependent on the angle, and the etching rate profile on the surface of the substrate (target object) is non-uniform.

[0043]

(Experimental example 2)

FIG. 21 is a list showing the evaluation result of an experimental example 2 (the case where the spacer is provided at the entire periphery). Part (a) of FIG. 21 shows a map showing an etching rate. Part (b) of FIG. 21 shows a graph showing a normalized etching rate. Part (c) of FIG. 21 shows the position into which the spacer is inserted.